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Renesas Technology Corp.
Customer Support Dept.
April 1, 2003

Cautions

Keep safety first in your circuit designs!

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Remember to give due consideration to safety when making your circuit designs, with appropriate measures such as (i) placement of substitutive, auxiliary circuits, (ii) use of nonflammable material or (iii) prevention against any malfunction or mishap.

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HD74HC133

13-input NAND Gate



ADE-205-442 (Z)
1st. Edition
Sep. 2000

Description

This device contains a single 13-input NAND gate. They perform the boolean functions in positive logic.

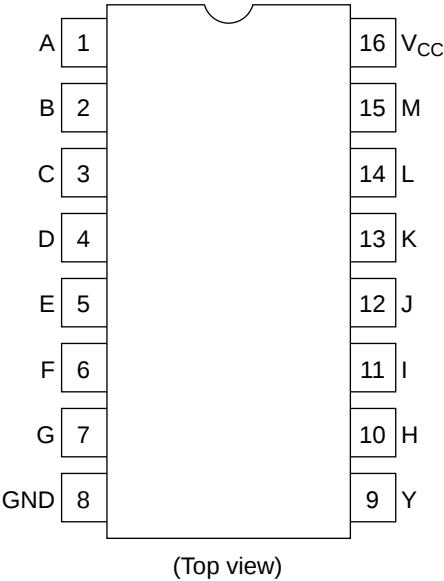
$$Y = \overline{A \cdot B \cdot C \cdot D \cdot E \cdot F \cdot G \cdot H \cdot I \cdot J \cdot K \cdot L \cdot M} \text{ or}$$

$$Y = \overline{A} + \overline{B} + \overline{C} + \overline{D} + \overline{E} + \overline{F} + \overline{G} + \overline{H} + \overline{I} + \overline{J} + \overline{K} + \overline{L} + \overline{M}$$

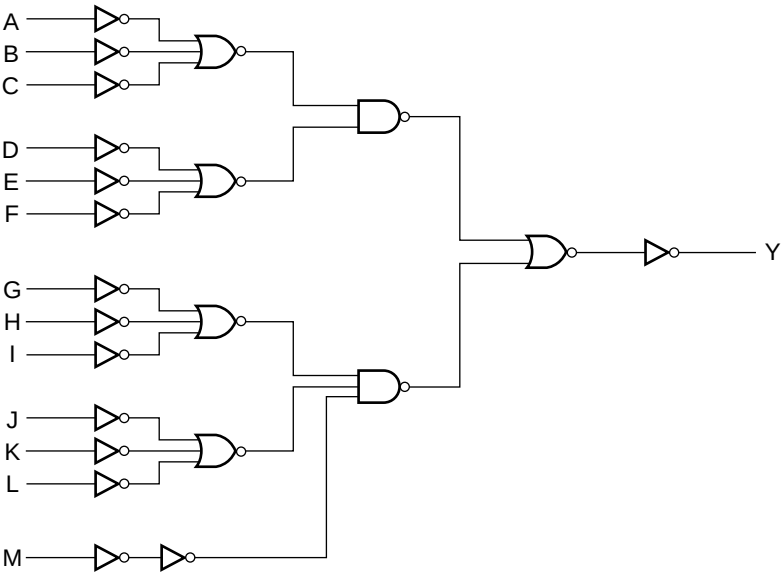
Features

- High Speed Operation: $t_{pd} = 12.5 \text{ ns typ (} C_L = 50 \text{ pF)}$
- High Output Current: Fanout of 10 LSTTL Loads
- Wide Operating Voltage: $V_{CC} = 2 \text{ to } 6 \text{ V}$
- Low Input Current: $1 \mu\text{A max}$
- Low Quiescent Supply Current: $I_{CC} \text{ (static)} = 1 \mu\text{A max (} T_a = 25^\circ\text{C)}$

Pin Arrangement



Logic Diagram



DC Characteristics

Item	Symbol	V _{CC} (V)	Ta = 25°C			Ta = -40 to +85°C		Unit	Test Conditions	
			Min	Typ	Max	Min	Max			
Input voltage	V _{IH}	2.0	1.5	—	—	1.5	—	V		
		4.5	3.15	—	—	3.15	—			
		6.0	4.2	—	—	4.2	—			
	V _{IL}	2.0	—	—	0.5	—	0.5	V		
		4.5	—	—	1.35	—	1.35			
		6.0	—	—	1.8	—	1.8			
Output voltage	V _{OH}	2.0	1.9	2.0	—	1.9	—	V	Vin = V _{IH} or V _{IL} I _{OH} = -20 μA	
		4.5	4.4	4.5	—	4.4	—			
		6.0	5.9	6.0	—	5.9	—			
		4.5	4.18	—	—	4.13	—			I _{OH} = -4 mA
		6.0	5.68	—	—	5.63	—			I _{OH} = -5.2 mA
	V _{OL}	2.0	—	0.0	0.1	—	0.1	V	Vin = V _{IH} or V _{IL} I _{OL} = 20 μA	
		4.5	—	0.0	0.1	—	0.1			
		6.0	—	0.0	0.1	—	0.1			
		4.5	—	—	0.26	—	0.33			I _{OL} = 4 mA
		6.0	—	—	0.26	—	0.33			I _{OL} = 5.2 mA
Input current	I _{in}	6.0	—	—	±0.1	—	±1.0	μA	Vin = V _{CC} or GND	
Quiescent supply current	I _{CC}	6.0	—	—	1.0	—	10	μA	Vin = V _{CC} or GND, I _{out} = 0 μA	

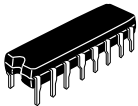
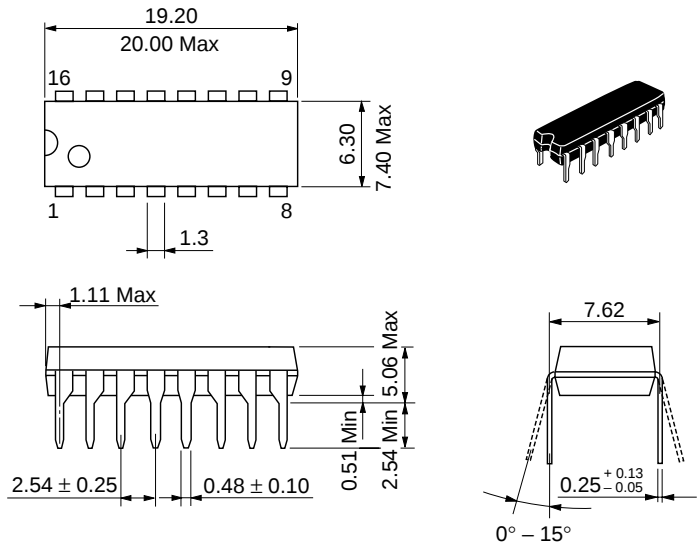
HD74HC133

AC Characteristics ($C_L = 50\text{ pF}$, Input $t_r = t_f = 6\text{ ns}$)

Item	Symbol	V _{CC} (V)	Ta = −40 to +85°C						Unit	Test Conditions
			Ta = 25°C							
			Min	Typ	Max	Min	Max			
Propagation delay time	t _{PLH}	2.0	—	—	150	—	190	ns		
		4.5	—	12	30	—	38			
		6.0	—	—	26	—	33			
	t _{PHL}	2.0	—	—	150	—	190	ns		
		4.5	—	13	30	—	38			
		6.0	—	—	26	—	33			
Output rise time	t _{TLH}	2.0	—	—	75	—	95	ns		
		4.5	—	5	15	—	19			
		6.0	—	—	13	—	16			
Output fall time	t _{THL}	2.0	—	—	75	—	95	ns		
		4.5	—	5	15	—	19			
		6.0	—	—	13	—	16			
Input capacitance	C _{in}	—	—	5	10	—	10	pF		

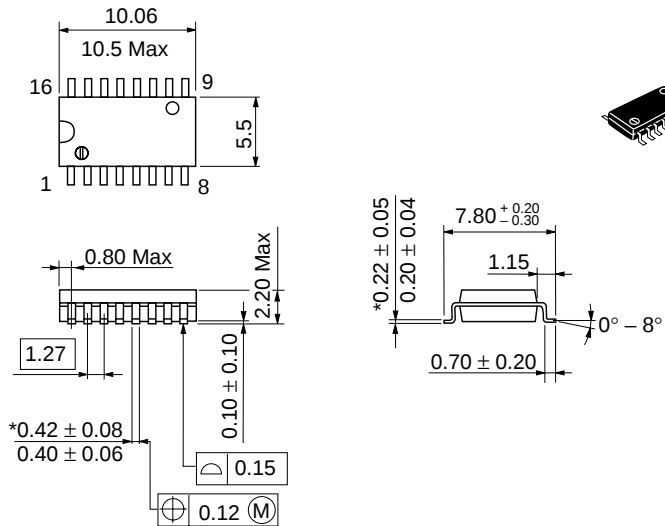
Package Dimensions

Unit: mm



Hitachi Code	DP-16
JEDEC	Conforms
EIAJ	Conforms
Mass (reference value)	1.07 g

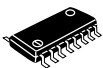
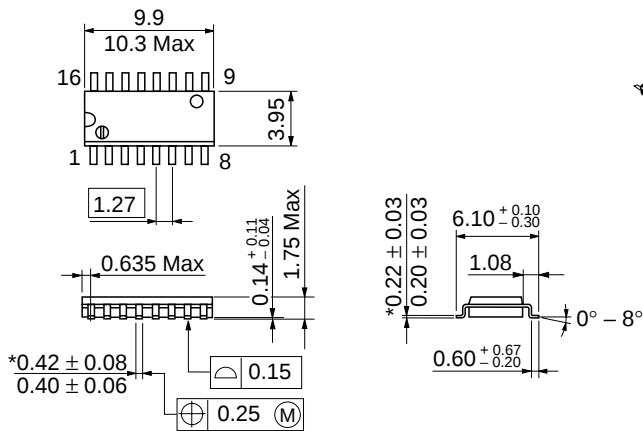
Unit: mm



*Dimension including the plating thickness
Base material dimension

Hitachi Code	FP-16DA
JEDEC	—
EIAJ	Conforms
Mass (reference value)	0.24 g

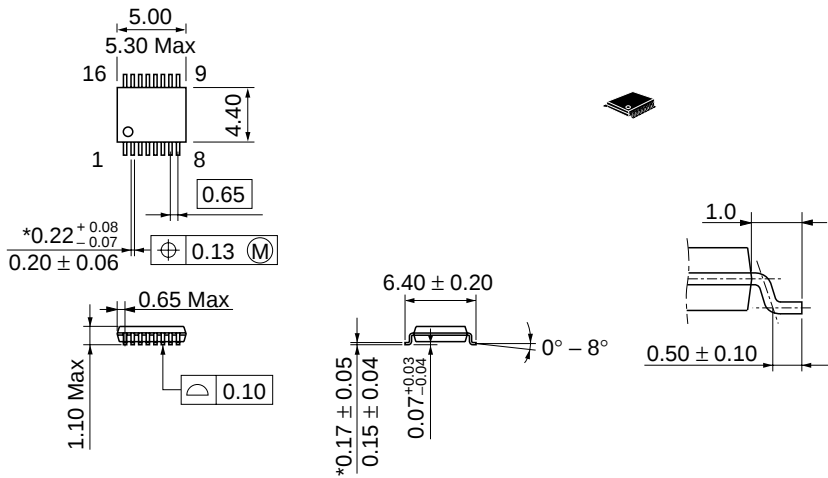
Unit: mm



*Dimension including the plating thickness
Base material dimension

Hitachi Code	FP-16DN
JEDEC	Conforms
EIAJ	Conforms
Mass (reference value)	0.15 g

Unit: mm



*Dimension including the plating thickness
Base material dimension

Hitachi Code	TTP-16DA
JEDEC	—
EIAJ	—
Mass (reference value)	0.05 g

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